

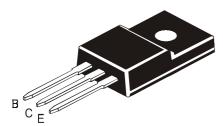
## Continental Device India Limited

An ISO/TS 16949, ISO 9001 and ISO 14001 Certified Company





## SILICON PLANAR POWER DARLINGTON TRANSISTORS



NPN PNP CJF100 CJF105 CJF101 CJF106 CJF102 CJF107

TO-220FP Fully Isolated Plastic Package

## **Power Darlington for Linear and Switching Applications**

#### **ABSOLUTE MAXIMUM RATINGS**

DESCRIPTION	SYMBOL	CJF100 CJF105	CJF101 CJF106	CJF102 CJF107	UNIT
Collector Base Voltage	V <sub>CBO</sub>	60	80	100	V
Collector Emitter Voltage	$V_{CEO}$	60	80	100	V
Emitter Base Voltage	$V_{EBO}$	5.0			V
RMS Isolation Voltage (for 1sec, R.H.	(1) V <sub>ISOL</sub> (a)	3500			$V_{RMS}$
<30%, T <sub>A</sub> =25°C )	(b)	1500			
Collector Current - Continuous	I <sub>C</sub>	8.0			Α
Peak	I <sub>CM</sub>	15			
Base Current	I <sub>B</sub>	1.0			Α
Total Power Dissipation @ T <sub>C</sub> =25°C	$P_{tot}$	80			W
Derate Above 25°C		0.64			W/°C
Total Power Dissipation @ T <sub>A</sub> =25°C	P <sub>tot</sub>	2.0			W
Derate Above 25°C		0.016			W/°C
Operating And Storage Junction	T <sub>j</sub> , T <sub>stg</sub>	- 65 to +150			°C
Temperature Range					

(1) RMS Isolation Voltage : (a) 3500 V<sub>RMS</sub> with Package in Clip Mounting Position (b) 1500 V<sub>RMS</sub> with Package in Screw Mounting Position (for 1sec, R.H.<30%Ta=25°C; Pulse Test: Pulse Width </=300µs, Duty Cycle</=2%)

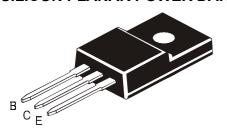
## THERMAL RESISTANCE

Characteristics	SYMBOL	MAX	UNIT
From Junction to Ambient	$R_{th(j-a)}$	62.5	°C/W
From Junction to Case	R <sub>th(j-c)</sub>	1.56	°C/W

## ELECTRICAL CHARACTERISTICS (T<sub>C</sub>=25°C unless specified otherwise)

DESCRIPTION	CRIPTION SYMBOL TEST CONDITION		MIN	MAX	UNIT
Collector Emitter Sustaining Voltage	V <sub>CEO (sus)</sub> *	I <sub>C</sub> =30mA, I <sub>B</sub> =0			
	, ,	CJF100/105	60	-	V
		CJF101/106	80	-	V
		CJF102/107	100	-	V
Collector Cut Off Current	I <sub>CEO</sub>	V <sub>CE</sub> = I/2 Rated V <sub>CEO</sub> , I <sub>B</sub> =0	-	50	μΑ
	I <sub>CBO</sub>	V <sub>CB</sub> = Rated V <sub>CBO</sub> , I <sub>E</sub> =0	-	50	μA
Emitter Cut Off Current	I <sub>EBO</sub>	$V_{EB}$ =5V, $I_{C}$ =0	-	8.0	mA

## SILICON PLANAR POWER DARLINGTON TRANSISTORS



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**TO-220FP Fully Isolated Plastic Package** 

## ELECTRICAL CHARACTERISTICS (T<sub>C</sub>=25°C unless specified otherwise)

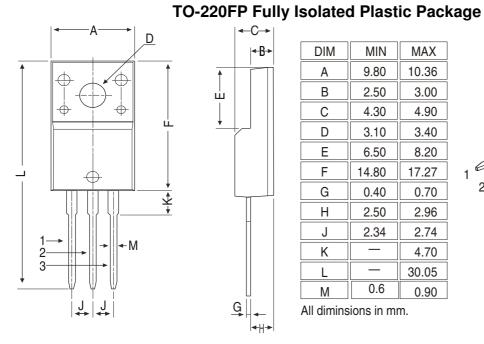
DESCRIPTION	SYMBOL	TEST CONDITION	MIN	MAX	UNIT
Collector Emitter Saturation Voltages	V <sub>CE (sat)</sub> *	I <sub>C</sub> =3A, I <sub>B</sub> =6mA I <sub>C</sub> =8A, I <sub>B</sub> =80mA	-	2.0 2.5	V
Base Emitter On Voltage	V <sub>BE (on)</sub> *	b=8A, V <sub>CE</sub> =4V	-	2.8	V
DC Current Gain	h <sub>FE</sub> *	$I_C$ =3A, $V_{CE}$ =4V	1000	20000	
		$I_C=8A, V_{CE}=4V$	200	-	

## **DYNAMIC CHARACTERISTICS**

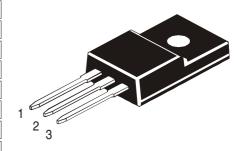
Small Signal Current Gain	lh <sub>fe</sub> l	I <sub>C</sub> =3A, V <sub>CE</sub> =4V,f=1MHz	4.0	-	
Output Capacitance	C <sub>o</sub>	V <sub>CB</sub> =10V, I <sub>E</sub> =0, f=0.1MHz			
		PNP	-	300	pF
		NPN	-	200	
Forward Voltage of Commutation Diode	V <sub>F</sub> *	$I_F = -I_C = 10A, I_B = 0$	-	6.0	V

<sup>\*</sup> Pulse Test: Pulse Width ≤ 300µs, Duty Cycle ≤ 2 %

**CJF100 CJF105** CJF101 CJF106 CJF102 CJF107



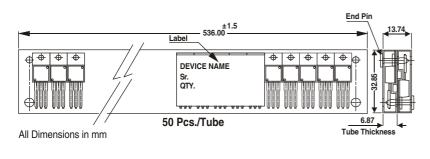
DIM	MIN	MAX					
Α	9.80	10.36					
В	2.50	3.00					
С	4.30	4.90					
D	3.10	3.40					
Е	6.50	8.20					
F	14.80	17.27					
G	0.40	0.70					
Н	2.50	2.96					
J	2.34	2.74					
K	_	4.70					
L	_	30.05					
М	0.6	0.90					
All diminsions in mm.							

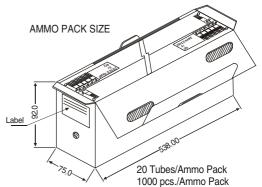


Pin Configuration

- 1. Base
- 2. Collector
- 3. Emitter

# **TO-220 FP Tube Packing**





# **Packing Detail**

PACKAGE	STANDARD PACK		INNER CARTON BOX		OUTER CARTON BOX		
	Details	Net Weight/Qty	Size Qty		Size	Qty	Gr Wt
TO-220FP	200 pcs/polybag	396 gm/200 pcs	3" x 7.5" x 7.5"	1K	17" x 15" x 13.5"	16K	36 kgs
	50 pcs/tube	135 gm/50 pcs	3.5" x 3.7" x 21.5"	1K	19" x 19" x 19"	10K	28 kgs

Notes

NPN PNP CJF100 CJF105 CJF101 CJF106 CJF102 CJF107

## **Component Disposal Instructions**

- 1. CDIL Semiconductor Devices are RoHS compliant, customers are requested to please dispose as per prevailing Environmental Legislation of their Country.
- 2. In Europe, please dispose as per EU Directive 2002/96/EC on Waste Electrical and Electronic Equipment (WEFE).

#### **Disclaimer**

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